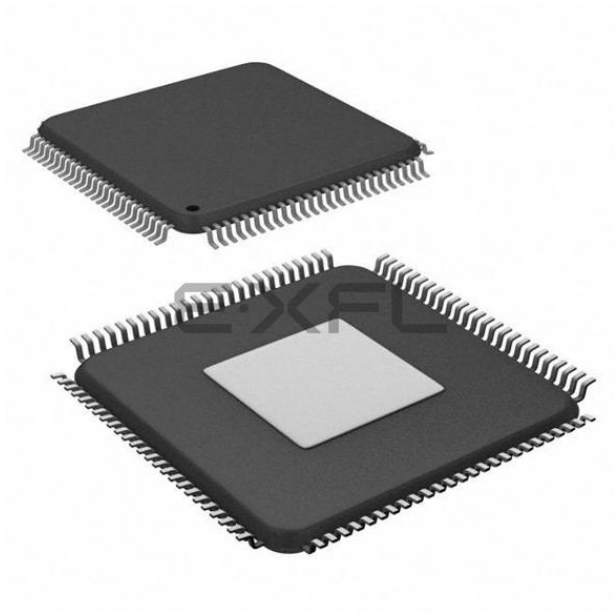
Infineon Technologies - SAK-XE164GN-16F80L AA Datasheet



Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	C166SV2
Core Size	16-Bit
Speed	80MHz
Connectivity	CANbus, EBI/EMI, I²C, LINbus, SPI, SSC, UART/USART, USI
Peripherals	I²S, POR, PWM, WDT
Number of I/O	75
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	18K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 11x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-100-8
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/sak-xe164gn-16f80l-aa

16-Bit

Architecture

XE164FN, XE164GN, XE164HN, XE164KN

16-Bit Single-Chip
Real Time Signal Controller
XE166 Family / Value Line

Data Sheet

V1.4 2013-02

Microcontrollers

Table of Contents

Table 5 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
57	P2.9	O0 / I	St/B	**Bit 9 of Port 2, General Purpose Input/Output**
	U0C1_DOUT	O1	St/B	**USIC0 Channel 1 Shift Data Output**
	TxDC1	O2	St/B	**CAN Node 1 Transmit Data Output**
	CC2_CC22	O3 / I	St/B	**CAPCOM2 CC22IO Capture Inp./ Compare Out.**
	A22	OH	St/B	**External Bus Interface Address Line 22**
	CLKIN1	I	St/B	**Clock Signal Input 1**
	TCK_A	IH	St/B	**DAP0/JTAG Clock Input** If JTAG pos. A is selected during start-up, an internal pull-up device will hold this pin high when nothing is driving it. If DAP pos. 0 is selected during start-up, an internal pull-down device will hold this pin low when nothing is driving it.
58	P0.2	O0 / I	St/B	**Bit 2 of Port 0, General Purpose Input/Output**
	U1C0_SCLKOUT	O1	St/B	**USIC1 Channel 0 Shift Clock Output**
	TxDC0	O2	St/B	**CAN Node 0 Transmit Data Output**
	CCU61_CC62	O3	St/B	**CCU61 Channel 2 Output**
	A2	OH	St/B	**External Bus Interface Address Line 2**
	U1C0_DX1B	I	St/B	**USIC1 Channel 0 Shift Clock Input**
	CCU61_CC62INA	I	St/B	**CCU61 Channel 2 Input**

Table 5 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
59	P10.0	O0 / I	St/B	**Bit 0 of Port 10, General Purpose Input/Output**
	U0C1_DOUT	O1	St/B	**USIC0 Channel 1 Shift Data Output**
	CCU60_CC60	O2	St/B	**CCU60 Channel 0 Output**
	AD0	OH / IH	St/B	**External Bus Interface Address/Data Line 0**
	CCU60_CC60INA	I	St/B	**CCU60 Channel 0 Input**
	ESR1_2	I	St/B	**ESR1 Trigger Input 2**
	U0C0_DX0A	I	St/B	**USIC0 Channel 0 Shift Data Input**
	U0C1_DX0A	I	St/B	**USIC0 Channel 1 Shift Data Input**
60	P10.1	O0 / I	St/B	**Bit 1 of Port 10, General Purpose Input/Output**
	U0C0_DOUT	O1	St/B	**USIC0 Channel 0 Shift Data Output**
	CCU60_CC61	O2	St/B	**CCU60 Channel 1 Output**
	AD1	OH / IH	St/B	**External Bus Interface Address/Data Line 1**
	CCU60_CC61INA	I	St/B	**CCU60 Channel 1 Input**
	U0C0_DX1A	I	St/B	**USIC0 Channel 0 Shift Clock Input**
	U0C0_DX0B	I	St/B	**USIC0 Channel 0 Shift Data Input**
61	P0.3	O0 / I	St/B	**Bit 3 of Port 0, General Purpose Input/Output**
	U1C0_SELO0	O1	St/B	**USIC1 Channel 0 Select/Control 0 Output**
	U1C1_SELO1	O2	St/B	**USIC1 Channel 1 Select/Control 1 Output**
	CCU61_COUT60	O3	St/B	**CCU61 Channel 0 Output**
	A3	OH	St/B	**External Bus Interface Address Line 3**
	U1C0_DX2A	I	St/B	**USIC1 Channel 0 Shift Control Input**
	RxDC0B	I	St/B	**CAN Node 0 Receive Data Input**

3.1 Memory Subsystem and Organization

The memory space of the XE164xN is configured in the von Neumann architecture. In this architecture all internal and external resources, including code memory, data memory, registers and I/O ports, are organized in the same linear address space.

Table 7 XE164xN Memory Map [1)]

Address Area	Start Loc.	End Loc.	Area Size[2)]	Notes
IMB register space	FF'FF00$_H$	FF'FFFF$_H$	256 Bytes	
Reserved	F0'0000$_H$	FF'FEFF$_H$	< 1 Mbyte	Minus IMB registers
Reserved for EPSRAM	E8'4000$_H$	EF'FFFF$_H$	496 Kbytes	Mirrors EPSRAM
Emulated PSRAM	E8'0000$_H$	E8'3FFF$_H$	up to 16 Kbytes	With Flash timing
Reserved for PSRAM	E0'4000$_H$	E7'FFFF$_H$	496 Kbytes	Mirrors PSRAM
PSRAM	E0'0000$_H$	E0'3FFF$_H$	up to 16 Kbytes	Program SRAM
Reserved for Flash	C5'0000$_H$	DF'FFFF$_H$	1,728 Kbytes	
Flash 1	C4'0000$_H$	C4'FFFF$_H$	64 Kbytes	
Flash 0	C0'0000$_H$	C3'FFFF$_H$	256 Kbytes[3)]	Minus res. seg.
External memory area	40'0000$_H$	BF'FFFF$_H$	8 Mbytes	
External IO area[4)]	21'0000$_H$	3F'FFFF$_H$	1,984 Kbytes	
Reserved	20'BC00$_H$	20'FFFF$_H$	17 Kbytes	
USIC0–2 alternate regs.	20'B000$_H$	20'BBFF$_H$	3 Kbytes	Accessed via EBC
MultiCAN alternate regs.	20'8000$_H$	20'AFFF$_H$	12 Kbytes	Accessed via EBC
Reserved	20'5800$_H$	20'7FFF$_H$	10 Kbytes	
USIC0–2 registers	20'4000$_H$	20'57FF$_H$	6 Kbytes	Accessed via EBC
Reserved	20'6800$_H$	20'7FFF$_H$	6 Kbytes	
MultiCAN registers	20'0000$_H$	20'3FFF$_H$	16 Kbytes	Accessed via EBC
External memory area	01'0000$_H$	1F'FFFF$_H$	1984 Kbytes	
SFR area	00'FE00$_H$	00'FFFF$_H$	0.5 Kbytes	
Dualport RAM (DPRAM)	00'F600$_H$	00'FDFF$_H$	2 Kbytes	
Reserved for DPRAM	00'F200$_H$	00'F5FF$_H$	1 Kbytes	
ESFR area	00'F000$_H$	00'F1FF$_H$	0.5 Kbytes	
XSFR area	00'E000$_H$	00'EFFF$_H$	4 Kbytes	
Data SRAM (DSRAM)	00'A000$_H$	00'DFFF$_H$	16 Kbytes	

3.8 Capture/Compare Unit (CC2)

The CAPCOM unit supports generation and control of timing sequences on up to 16 channels with a maximum resolution of one system clock cycle (eight cycles in staggered mode). The CAPCOM unit is typically used to handle high-speed I/O tasks such as pulse and waveform generation, pulse width modulation (PWM), digital to analog (D/A) conversion, software timing, or time recording with respect to external events.

Two 16-bit timers with reload registers provide two independent time bases for the capture/compare register array.

The input clock for the timers is programmable to several prescaled values of the internal system clock, or may be derived from an overflow/underflow of timer T6 in module GPT2. This provides a wide range of variation for the timer period and resolution and allows precise adjustments to the application specific requirements. In addition, external count inputs allow event scheduling for the capture/compare registers relative to external events.

The capture/compare register array contains 16 dual purpose capture/compare registers, each of which may be individually allocated to either CAPCOM timer and programmed for capture or compare function.
All registers have each one port pin associated with it which serves as an input pin for triggering the capture function, or as an output pin to indicate the occurrence of a compare event.

When a capture/compare register has been selected for capture mode, the current contents of the allocated timer will be latched (‘captured’) into the capture/compare register in response to an external event at the port pin which is associated with this register. In addition, a specific interrupt request for this capture/compare register is generated. Either a positive, a negative, or both a positive and a negative external signal transition at the pin can be selected as the triggering event.

The contents of all registers which have been selected for one of the five compare modes are continuously compared with the contents of the allocated timers.

When a match occurs between the timer value and the value in a capture/compare register, specific actions will be taken based on the selected compare mode.

Table 8 Compare Modes

Compare Modes	Function
Mode 0	Interrupt-only compare mode; Several compare interrupts per timer period are possible
Mode 1	Pin toggles on each compare match; Several compare events per timer period are possible

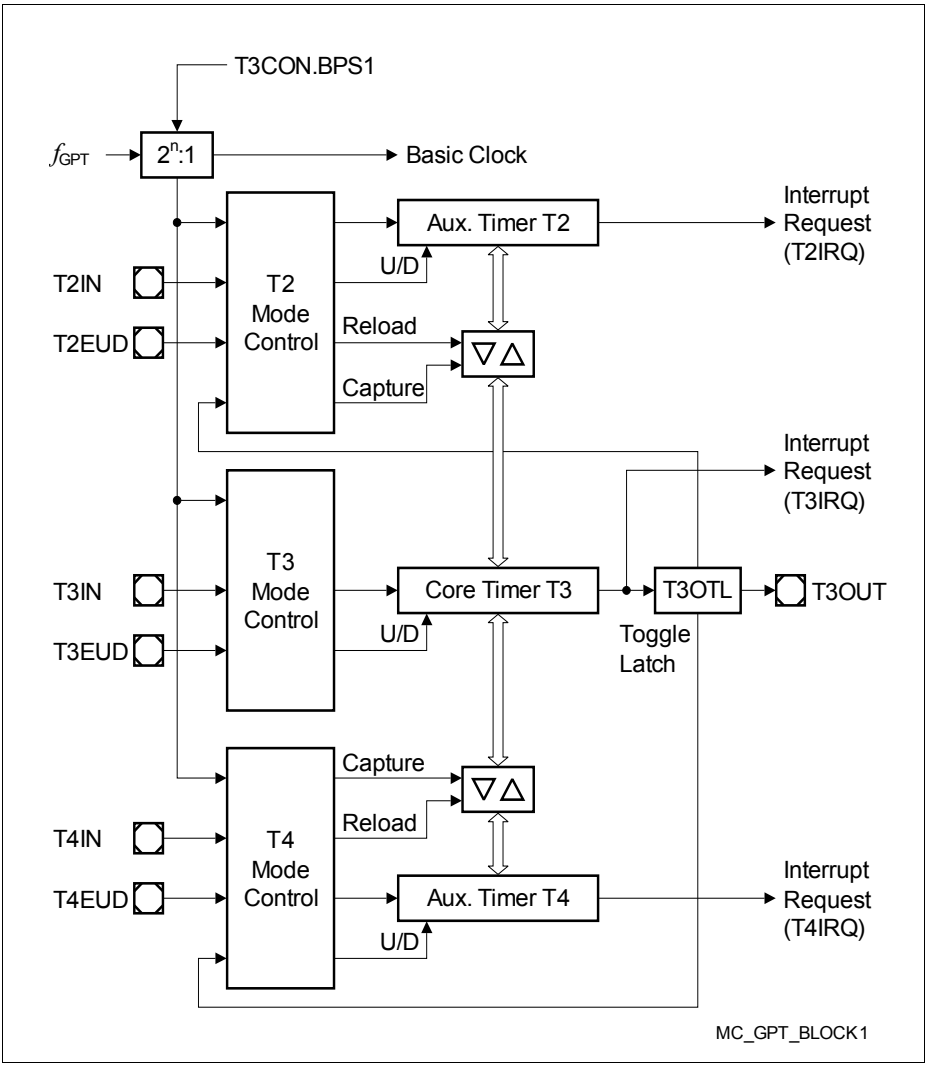


Figure 8 Block Diagram of GPT1

3.12 A/D Converters

For analog signal measurement, up to two 10-bit A/D converters (ADC0, ADC1) with 11 + 5 multiplexed input channels and a sample and hold circuit have been integrated on-chip. 4 inputs can be converted by both A/D converters. Conversions use the successive approximation method. The sample time (to charge the capacitors) and the conversion time are programmable so that they can be adjusted to the external circuit. The A/D converters can also operate in 8-bit conversion mode, further reducing the conversion time.

Several independent conversion result registers, selectable interrupt requests, and highly flexible conversion sequences provide a high degree of programmability to meet the application requirements. Both modules can be synchronized to allow parallel sampling of two input channels.

For applications that require more analog input channels, external analog multiplexers can be controlled automatically. For applications that require fewer analog input channels, the remaining channel inputs can be used as digital input port pins.

The A/D converters of the XE164xN support two types of request sources which can be triggered by several internal and external events.

- Parallel requests are activated at the same time and then executed in a predefined sequence.
- Queued requests are executed in a user-defined sequence.

In addition, the conversion of a specific channel can be inserted into a running sequence without disturbing that sequence. All requests are arbitrated according to the priority level assigned to them.

Data reduction features reduce the number of required CPU access operations allowing the precise evaluation of analog inputs (high conversion rate) even at a low CPU speed. Result data can be reduced by limit checking or accumulation of results.

The Peripheral Event Controller (PEC) can be used to control the A/D converters or to automatically store conversion results to a table in memory for later evaluation, without requiring the overhead of entering and exiting interrupt routines for each data transfer. Each A/D converter contains eight result registers which can be concatenated to build a result FIFO. Wait-for-read mode can be enabled for each result register to prevent the loss of conversion data.

In order to decouple analog inputs from digital noise and to avoid input trigger noise, those pins used for analog input can be disconnected from the digital input stages. This can be selected for each pin separately with the Port x Digital Input Disable registers.

The Auto-Power-Down feature of the A/D converters minimizes the power consumption when no conversion is in progress.

Broken wire detection for each channel and a multiplexer test mode provide information to verify the proper operation of the analog signal sources (e.g. a sensor system).

3.18 Parallel Ports

The XE164xN provides up to 76 I/O lines which are organized into 7 input/output ports and 2 input ports. All port lines are bit-addressable, and all input/output lines can be individually (bit-wise) configured via port control registers. This configuration selects the direction (input/output), push/pull or open-drain operation, activation of pull devices, and edge characteristics (shape) and driver characteristics (output current) of the port drivers. The I/O ports are true bidirectional ports which are switched to high impedance state when configured as inputs. During the internal reset, all port pins are configured as inputs without pull devices active.

All port lines have alternate input or output functions associated with them. These alternate functions can be programmed to be assigned to various port pins to support the best utilization for a given application. For this reason, certain functions appear several times in **Table 9**.

All port lines that are not used for alternate functions may be used as general purpose I/O lines.

Table 9 Summary of the XE164xN's Ports

Port	Width	I/O	Connected Modules
P0	8	I/O	EBC (A7...A0), CCU6, USIC, CAN
P1	8	I/O	EBC (A15...A8), CCU6, USIC
P2	14	I/O	EBC (READY, $\overline{\text{BHE}}$, A23...A16, AD15...AD13, D15...D13), CAN, CC2, GPT12E, USIC, DAP/JTAG
P4	4	I/O	EBC ($\overline{\text{CS3}}$...$\overline{\text{CS0}}$), CC2, CAN, GPT12E, USIC
P5	11	I	Analog Inputs, CCU6, DAP/JTAG, GPT12E, CAN
P6	3	I/O	ADC, CAN, GPT12E
P7	5	I/O	CAN, GPT12E, SCU, DAP/JTAG, CCU6, ADC, USIC
P10	16	I/O	EBC (ALE, $\overline{\text{RD}}$, $\overline{\text{WR}}$, AD12...AD0, D12...D0), CCU6, USIC, DAP/JTAG, CAN
P15	5	I	Analog Inputs, GPT12E

7) An overload current (I_{OV}) through a pin injects a certain error current (I_{INJ}) into the adjacent pins. This error current adds to the respective pins leakage current (I_{OZ}). The amount of error current depends on the overload current and is defined by the overload coupling factor K_{OV}. The polarity of the injected error current is inverse compared to the polarity of the overload current that produces it.The total current through a pin is $|I_{TOT}| = |I_{OZ}| + (|I_{OV}| \ K_{OV})$. The additional error current may distort the input voltage on analog inputs.

8) Value is controlled by on-chip regulator

4.2 Voltage Range definitions

The XE164xN timing depends on the supply voltage. If such a dependency exists the timing values are given for 2 voltage areas commonly used. The voltage areas are defined in the following tables.

Table 13 Upper Voltage Range Definition

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Digital supply voltage for IO pads and voltage regulators	V_{DDP} SR	4.5	5	5.5	V	

Table 14 Lower Voltage Range Definition

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Digital supply voltage for IO pads and voltage regulators	V_{DDP} SR	3.0	3.3	4.5	V	

4.2.1 Parameter Interpretation

The parameters listed in the following include both the characteristics of the XE164xN and its demands on the system. To aid in correctly interpreting the parameters when evaluating them for a design, they are marked accordingly in the column “Symbol”:

CC (**C**ontroller **C**haracteristics):
The logic of the XE164xN provides signals with the specified characteristics.

SR (**S**ystem **R**equirement):
The external system must provide signals with the specified characteristics to the XE164xN.

4.3.1 DC Parameters for Upper Voltage Area

Keeping signal levels within the limits specified in this table ensures operation without overload conditions. For signal levels outside these specifications, also refer to the specification of the overload current I_{OV}.

Note: Operating Conditions apply.

Table 15 is valid under the following conditions: $V_{DDP} \leq$ 5.5 V; V_{DDP}typ. 5 V; $V_{DDP} \geq$ 4.5 V

Table 15 DC Characteristics for Upper Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Pin capacitance (digital inputs/outputs). To be doubled for double bond pins.[1)]	C_{IO} CC	–	–	10	pF	not subject to production test
Input Hysteresis[2)]	HYS CC	0.11 x V_{DDP}	–	–	V	R_S= 0 Ohm
Absolute input leakage current on pins of analog ports[3)]	$\|I_{OZ1}\|$ CC	–	10	200	nA	$V_{IN} > V_{SS}$; $V_{IN} < V_{DDP}$
Absolute input leakage current for all other pins. To be doubled for double bond pins.[3)1)4)]	$\|I_{OZ2}\|$ CC	–	0.2	5	µA	$T_J \leq$ 110 °C; $V_{IN} > V_{SS}$; $V_{IN} < V_{DDP}$
		–	0.2	15	µA	$T_J \leq$ 150 °C; $V_{IN} > V_{SS}$; $V_{IN} < V_{DDP}$
Pull Level Force Current[5)]	$\|I_{PLF}\|$ SR	250	–	–	µA	$V_{IN} \geq V_{IHmin}$*(pull down_enabled)*; $V_{IN} \leq V_{ILmax}$*(pull up_enabled)*
Pull Level Keep Current[6)]	$\|I_{PLK}\|$ SR	–	–	30	µA	$V_{IN} \geq V_{IHmin}$*(pull up_enabled)*; $V_{IN} \leq V_{ILmax}$*(pull down_enabled)*
Input high voltage (all except XTAL1)	V_{IH} SR	0.7 x V_{DDP}	–	V_{DDP} + 0.3	V	
Input low voltage (all except XTAL1)	V_{IL} SR	-0.3	–	0.3 x V_{DDP}	V	

4) The broken wire detection delay against V_{AREF} is measured in numbers of consecutive precharge cycles at a conversion rate of not more than 10 µs. This function is influenced by leakage current, in particular at high temperature. Result above 80% (332_H)
5) TUE is tested at V_{AREF} = V_{DDPA} = 5.0 V, V_{AGND} = 0 V. It is verified by design for all other voltages within the defined voltage range. The specified TUE is valid only if the absolute sum of input overload currents on analog port pins (see I_{OV} specification) does not exceed 10 mA, and if V_{AREF} and V_{AGND} remain stable during the measurement time.
6) V_{AIN} may exceed V_{AGND} or V_{AREF} up to the absolute maximum ratings. However, the conversion result in these cases will be $X000_H$ or $X3FF_H$, respectively.

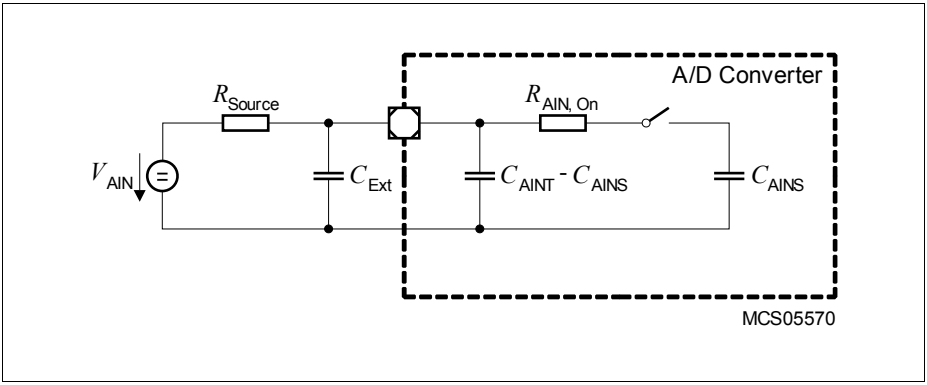


Figure 16 Equivalent Circuitry for Analog Inputs

4.6 Flash Memory Parameters

The XE164xN is delivered with all Flash sectors erased and with no protection installed.

The data retention time of the XE164xN's Flash memory (i.e. the time after which stored data can still be retrieved) depends on the number of times the Flash memory has been erased and programmed.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 24 Flash Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Parallel Flash module program/erase limit depending on Flash read activity	N_{PP} SR	–	–	2[1)]		$N_{FL\_RD} \leq 1$
		–	–	1[2)]		$N_{FL\_RD} > 1$
Flash erase endurance for security pages	N_{SEC} SR	10	–	–	cycles	$t_{RET} \geq$ 20 years
Flash wait states[3)]	$N_{WSFLASH}$ SR	1	–	–		$f_{SYS} \leq$ 8 MHz
		2	–	–		$f_{SYS} \leq$ 13 MHz
		3	–	–		$f_{SYS} \leq$ 17 MHz
		4	–	–		$f_{SYS} >$ 17 MHz
Erase time per sector/page	t_{ER} CC	–	7[4)]	8.0	ms	
Programming time per page	t_{PR} CC	–	3[4)]	3.5	ms	
Data retention time	t_{RET} CC	20	–	–	years	$N_{ER} \leq$ 1,000 cycles
Drain disturb limit	N_{DD} SR	32	–	–	cycles	
Number of erase cycles	N_{ER} SR	–	–	15.000	cycles	$t_{RET} \geq$ 5 years; Valid for Flash module 1 (up to 64 kbytes)
		–	–	1.000	cycles	$t_{RET} \geq$ 20 years

1) The unused Flash module(s) can be erased/programmed while code is executed and/or data is read from only one Flash module or from PSRAM. The Flash module that delivers code/data can, of course, not be erased/programmed.

4.7.5 External Bus Timing

The following parameters specify the behavior of the XE164xN bus interface.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 29 Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
CLKOUT Cycle Time[1)]	t_5 CC	–	1 / f_{SYS}	–	ns	
CLKOUT high time	t_6 CC	3	–	–		
CLKOUT low time	t_7 CC	3	–	–		
CLKOUT rise time	t_8 CC	–	–	3	ns	
CLKOUT fall time	t_9 CC	–	–	3		

1) The CLKOUT cycle time is influenced by PLL jitter. For longer periods the relative deviation decreases (see PLL deviation formula).

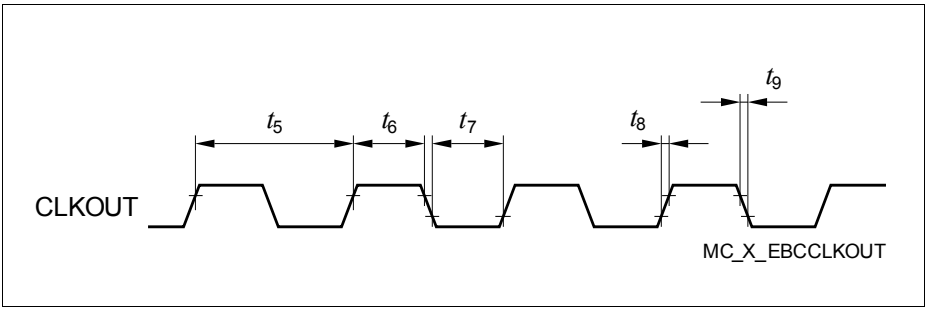


Figure 22 CLKOUT Signal Timing

Note: The term CLKOUT refers to the reference clock output signal which is generated by selecting f_{SYS} as the source signal for the clock output signal EXTCLK on pin P2.8 and by enabling the high-speed clock driver on this pin.

Variable Memory Cycles

External bus cycles of the XE164xN are executed in five consecutive cycle phases (AB, C, D, E, F). The duration of each cycle phase is programmable (via the TCONCSx registers) to adapt the external bus cycles to the respective external module (memory, peripheral, etc.).

The duration of the access phase can optionally be controlled by the external module using the READY handshake input.

This table provides a summary of the phases and the ranges for their length.

Table 30 Programmable Bus Cycle Phases (see timing diagrams)

Bus Cycle Phase	Parameter	Valid Values	Unit
Address setup phase, the standard duration of this phase (1 … 2 TCS) can be extended by 0 … 3 TCS if the address window is changed	tpAB	1 … 2 (5)	TCS
Command delay phase	tpC	0 … 3	TCS
Write Data setup/MUX Tristate phase	tpD	0 … 1	TCS
Access phase	tpE	1 … 32	TCS
Address/Write Data hold phase	tpF	0 … 3	TCS

Note: The bandwidth of a parameter (from minimum to maximum value) covers the whole operating range (temperature, voltage) as well as process variations. Within a given device, however, this bandwidth is smaller than the specified range. This is also due to interdependencies between certain parameters. Some of these interdependencies are described in additional notes (see standard timing).

Note: Operating Conditions apply.

Table 31 is valid under the following conditions: C_L= 20 pF; voltage_range= upper ; voltage_range= upper

Table 31 External Bus Timing for Upper Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Output valid delay for $\overline{RD}$, $\overline{WR}$($\overline{L}$/$\overline{H}$)	t_{10} CC	–	7	13	ns	
Output valid delay for $\overline{BHE}$, ALE	t_{11} CC	–	7	14	ns	
Address output valid delay for A23 ... A0	t_{12} CC	–	8	14	ns	

Table 31 External Bus Timing for Upper Voltage Range (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Address output valid delay for AD15 ... AD0 (MUX mode)	t_{13} CC	–	8	15	ns	
Output valid delay for $\overline{CS}$	t_{14} CC	–	7	13	ns	
Data output valid delay for AD15 ... AD0 (write data, MUX mode)	t_{15} CC	–	8	15	ns	
Data output valid delay for D15 ... D0 (write data, DEMUX mode)	t_{16} CC	–	8	15	ns	
Output hold time for $\overline{RD}$, $\overline{WR}$($\overline{L}$/$\overline{H}$)	t_{20} CC	-2	6	8	ns	
Output hold time for $\overline{BHE}$, ALE	t_{21} CC	-2	6	10	ns	
Address output hold time for AD15 ... AD0	t_{23} CC	-3	6	8	ns	
Output hold time for $\overline{CS}$	t_{24} CC	-3	6	11	ns	
Data output hold time for D15 ... D0 and AD15 ... AD0	t_{25} CC	-3	6	8	ns	
Input setup time for READY, D15 ... D0, AD15 ... AD0	t_{30} SR	25	15	–	ns	
Input hold time READY, D15 ... D0, AD15 ... AD0[1)]	t_{31} SR	0	-7	–	ns	

1) Read data are latched with the same internal clock edge that triggers the address change and the rising edge of RD. Address changes before the end of RD have no impact on (demultiplexed) read cycles. Read data can change after the rising edge of RD.

Table 32 is valid under the following conditions: C_L= 20 pF; voltage_range= lower ; voltage_range= lower

4.7.6 Synchronous Serial Interface Timing

The following parameters are applicable for a USIC channel operated in SSC mode.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 33 is valid under the following conditions: C_L= 20 pF; SSC= master ; voltage_range= upper

Table 33 USIC SSC Master Mode Timing for Upper Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Slave select output SELO active to first SCLKOUT transmit edge	t_1 CC	t_{SYS} - 8[1)]	–	–	ns	
Slave select output SELO inactive after last SCLKOUT receive edge	t_2 CC	t_{SYS} - 6[1)]	–	–	ns	
Data output DOUT valid time	t_3 CC	-6	–	9	ns	
Receive data input setup time to SCLKOUT receive edge	t_4 SR	31	–	–	ns	
Data input DX0 hold time from SCLKOUT receive edge	t_5 SR	-4	–	–	ns	

1) $t_{SYS} = 1 / f_{SYS}$

Table 34 is valid under the following conditions: C_L= 20 pF; SSC= master ; voltage_range= lower

4.7.7 Debug Interface Timing

The debugger can communicate with the XE164xN either via the 2-pin DAP interface or via the standard JTAG interface.

Debug via DAP

The following parameters are applicable for communication through the DAP debug interface.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 37 is valid under the following conditions: C_L= 20 pF; voltage_range= upper

Table 37 DAP Interface Timing for Upper Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
DAP0 clock period[1)]	t_{11} SR	25	–	–	ns	
DAP0 high time	t_{12} SR	8	–	–	ns	
DAP0 low time[1)]	t_{13} SR	8	–	–	ns	
DAP0 clock rise time	t_{14} SR	–	–	4	ns	
DAP0 clock fall time	t_{15} SR	–	–	4	ns	
DAP1 setup to DAP0 rising edge	t_{16} SR	6	–	–	ns	
DAP1 hold after DAP0 rising edge	t_{17} SR	6	–	–	ns	
DAP1 valid per DAP0 clock period[2)]	t_{19} CC	17	20	–	ns	

1) See the DAP chapter for clock rate restrictions in the Active::IDLE protocol state.

2) The Host has to find a suitable sampling point by analyzing the sync telegram response.

Table 38 is valid under the following conditions: C_L= 20 pF; voltage_range= lower

Table 38 DAP Interface Timing for Lower Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
DAP0 clock period[1]	t_{11} SR	25	–	–	ns	
DAP0 high time	t_{12} SR	8	–	–	ns	
DAP0 low time[1]	t_{13} SR	8	–	–	ns	
DAP0 clock rise time	t_{14} SR	–	–	4	ns	
DAP0 clock fall time	t_{15} SR	–	–	4	ns	
DAP1 setup to DAP0 rising edge	t_{16} SR	6	–	–	ns	
DAP1 hold after DAP0 rising edge	t_{17} SR	6	–	–	ns	
DAP1 valid per DAP0 clock period[2]	t_{19} CC	12	17	–	ns	

1) See the DAP chapter for clock rate restrictions in the Active::IDLE protocol state.

2) The Host has to find a suitable sampling point by analyzing the sync telegram response.

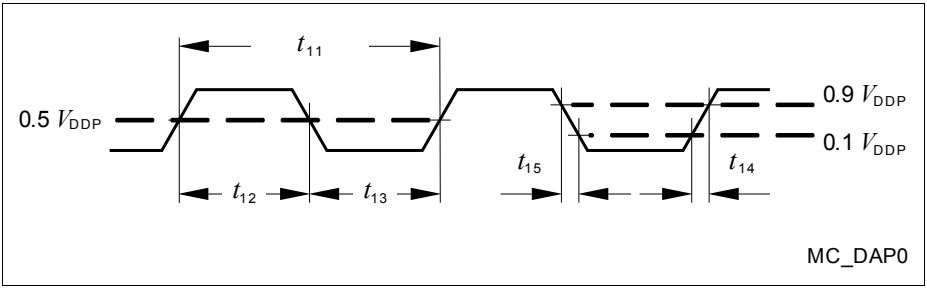


Figure 27 Test Clock Timing (DAP0)

5.3 Quality Declarations

The operation lifetime of the XE164xN depends on the operating temperature. The life time decreases with increasing temperature as shown in **Table 43**.

Table 42 Quality Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Operation lifetime	t_{OP} CC	–	–	20	a	See **Table 43**
ESD susceptibility according to Human Body Model (HBM)	V_{HBM} SR	–	–	2 000	V	EIA/JESD22-A114-B
Moisture sensitivity level	MSL CC	–	–	3	–	JEDEC J-STD-020C

Table 43 Lifetime dependency from Temperature

Operating Time	Operating Temperature
20 a	$T_J \leq 110°C$
95 500 h	$T_J = 120°C$
68 500 h	$T_J = 125°C$
49 500 h	$T_J = 130°C$
26 400 h	$T_J = 140°C$
14 500 h	$T_J = 150°C$